

Description

The SX150N04D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 40V$ $I_D = 150 A$

$R_{DS(ON)} < 2.4m\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings (TC=25°C unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	150	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	90	A
IDM	Pulsed Drain Current ²	450	A
EAS	Single Pulse Avalanche Energy ³	400	mJ
IAS	Avalanche Current	40	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation ⁴	125	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
R_{eJA}	Thermal Resistance Junction-Ambient ¹	50	°C/W
R_{eJC}	Thermal Resistance Junction-Case ¹	1	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	40	---	---	V
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=10\text{V}$, $I_D=20\text{A}$	---	2.0	2.3	
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=4.5\text{V}$, $I_D=20\text{A}$	---	2.7	3.0	$\text{m}\Omega$
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$	1.2	1.6	2.2	V
IDSS	Drain-Source Leakage Current	$V_{DS}=32\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=20\text{A}$	---	53	---	S
R_g	Gate Resistance	$V_{DS}=0\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	1.0	---	Ω
Qg	Total Gate Charge (4.5V)	$V_{DS}=15\text{V}$, $V_{GS}=10\text{V}$, $I_D=20\text{A}$	---	45	---	nC
Qgs	Gate-Source Charge		---	12	---	
Qgd	Gate-Drain Charge		---	18.5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=15\text{V}$, $V_{GS}=10\text{V}$, $R_G=3.3$, $I_D=20\text{A}$	---	18.5	---	ns
T_r	Rise Time		---	9	---	
Td(off)	Turn-Off Delay Time		---	58.5	---	
T_f	Fall Time		---	32	---	
Ciss	Input Capacitance	$V_{DS}=20\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	3972	---	pF
Coss	Output Capacitance		---	1119	---	
Crss	Reverse Transfer Capacitance		---	82	---	
IS	Continuous Source Current ^{1,6}	$V_G=V_D=0\text{V}$, Force Current	---	---	100	A
VSD	Diode Forward Voltage ²	$V_{GS}=0\text{V}$, $I_S=1\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25\text{V}$, $V_{GS}=10\text{V}$, $L=0.5\text{mH}$, $I_{AS}=40\text{A}$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

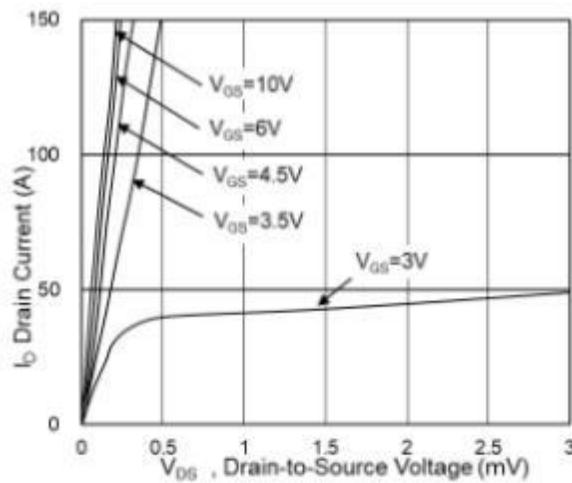


Fig.1 Typical Output Characteristics

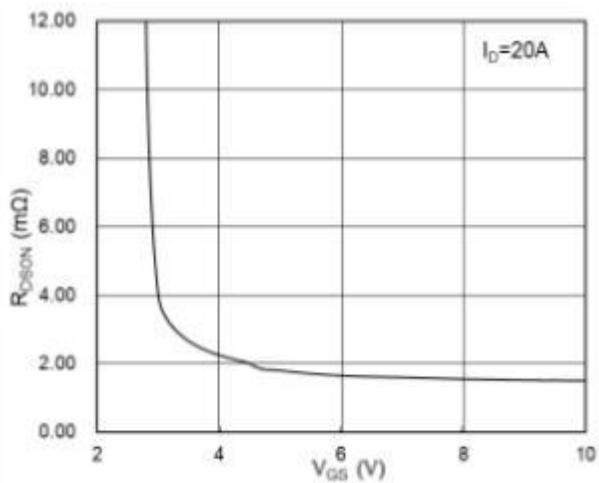


Fig.2 On-Resistance vs G-S Voltage

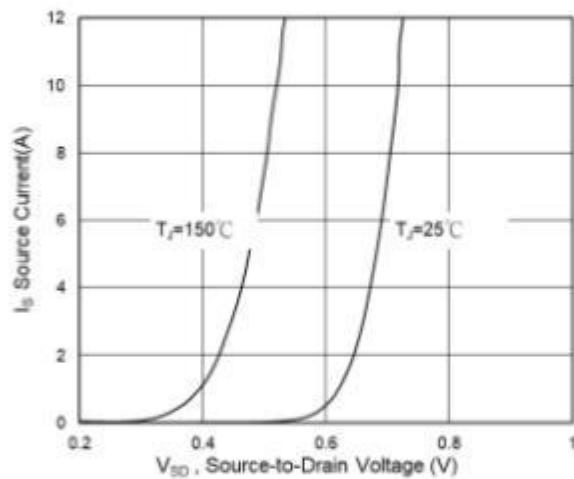


Fig.3 Source Drain Forward Characteristics

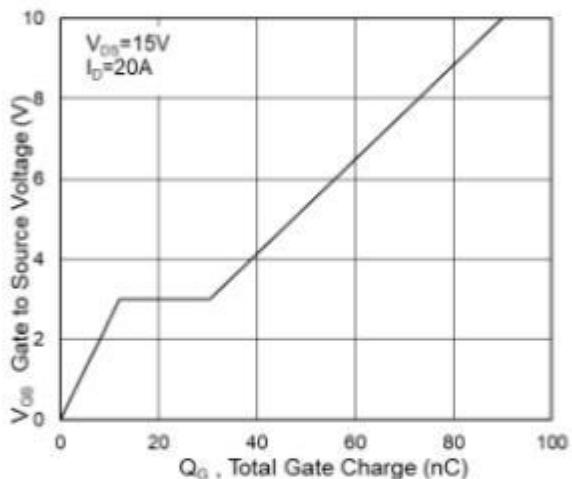


Fig.4 Gate-Charge Characteristics

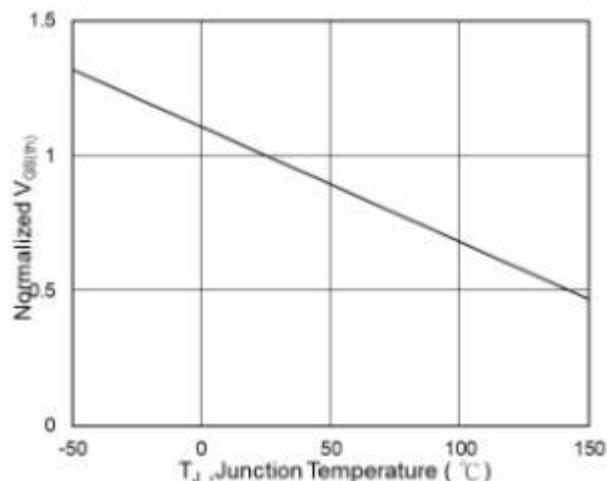


Fig.5 Normalized $V_{GS(th)}$ vs T_J

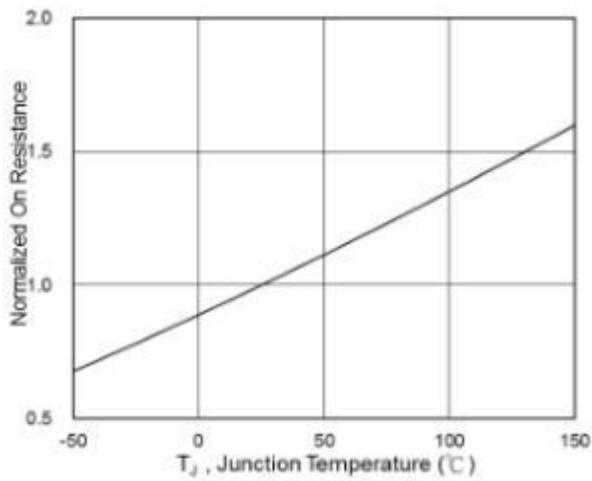


Fig.6 Normalized $R_{DS(on)}$ vs T_J

Typical Characteristics

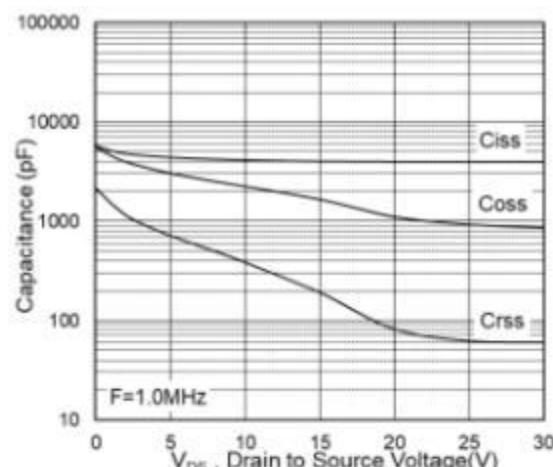


Fig.7 Capacitance

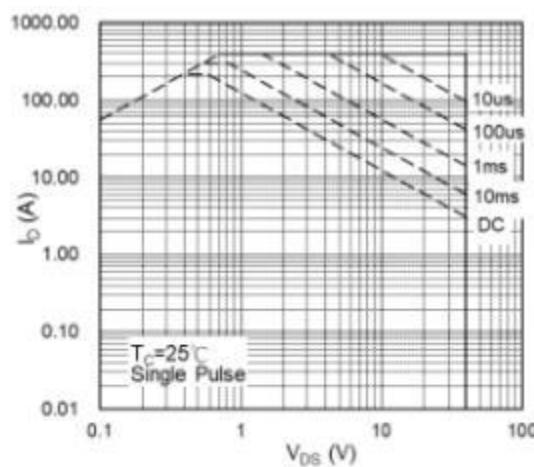


Fig.8 Safe Operating Area

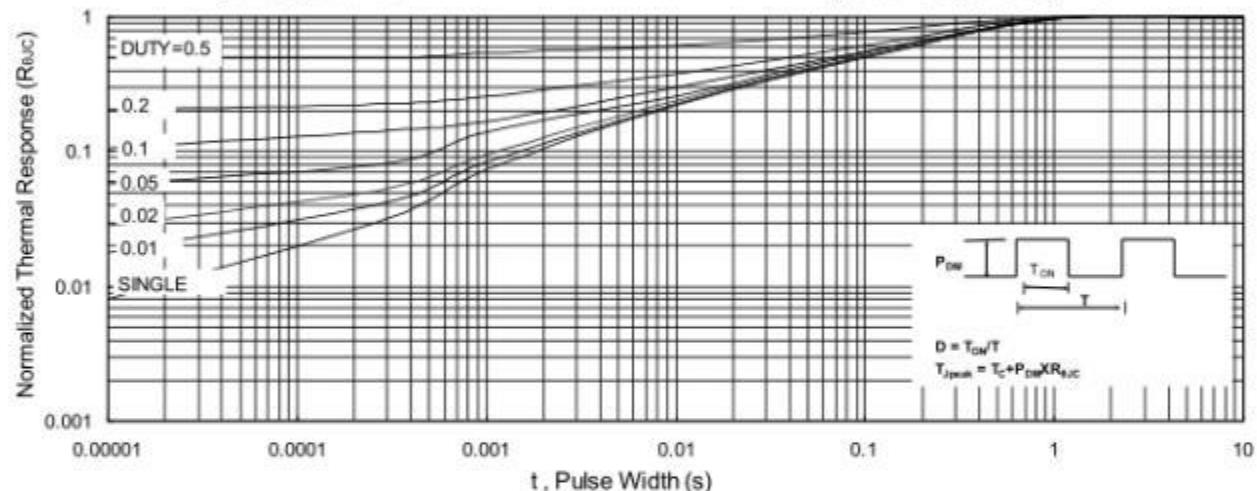


Fig.9 Normalized Maximum Transient Thermal Impedance

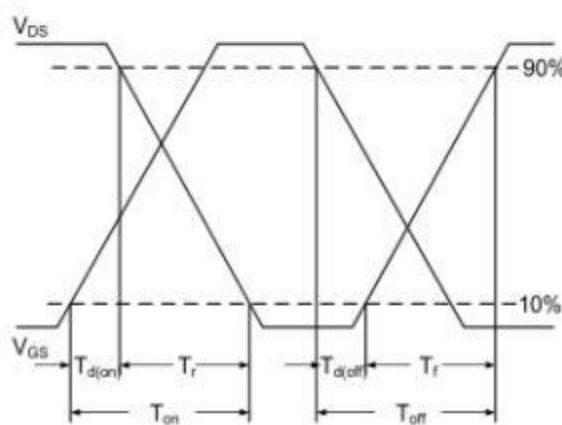


Fig.10 Switching Time Waveform

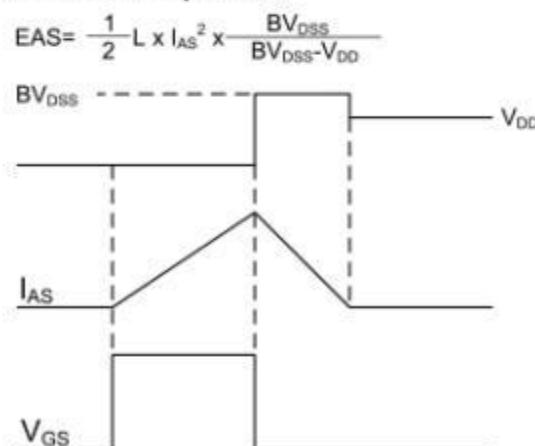
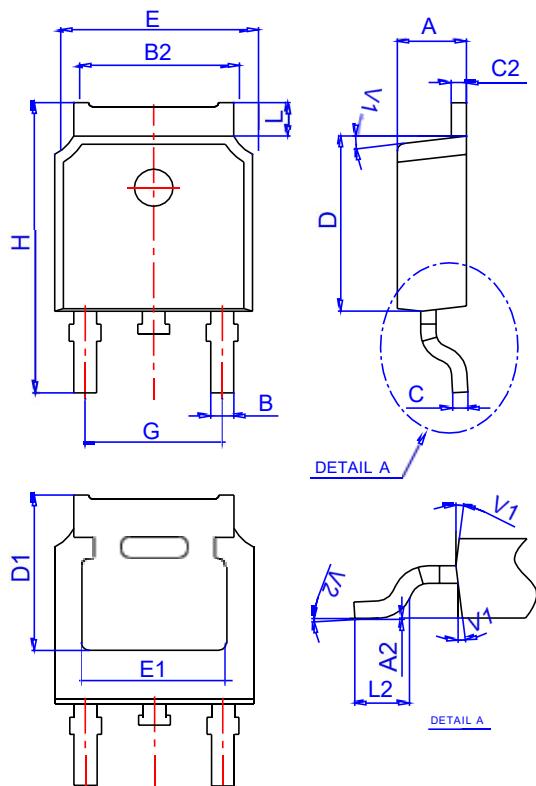


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data : TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500